In the Claims

Claims 32-48 are pending in the application with claims 32 and 38 amended herein.

Claims 1-31 (canceled).

32. (currently amended) A method comprising cleaning an accumulated deposition from a vaporization surface [[of]] where a non-vapor state material is converted to a vapor-state in a vapor forming device by using the vaporization surface as an electrode to form a plasma within the device.

33. (previously presented) The method of claim 32 wherein the vaporization surface is held at ground potential while RF energy is supplied to a second electrode to form the plasma.

34. (previously presented) The method of claim 32 wherein RF energy is supplied to the vaporization surface while a second electrode is held at ground potential to form the plasma.

35. (previously presented) The method of claim 32 wherein the vaporization surface is provided with a negative bias power while RF energy is supplied to a second electrode to form the plasma.

36. (previously presented) The method of claim 32 wherein the plasma comprises one or more of gaseous Cl_2, CCl_4 and CF_4.

37. (previously presented) The method of claim 32 wherein the device is comprised by a chemical vapor deposition apparatus.

38. (currently amended) A method of cleaning a vaporization surface having deposits accumulated from use in a vapor forming device, the method comprising using the vaporization surface where a non-vapor state material is converted to a vapor-state as an electrode to form a plasma within the device, the plasma cleaning at least some of the deposits from the vaporization surface.

39. (previously presented) The method of claim 38 wherein the vaporization surface is held at ground potential while RF energy is supplied to a second electrode to form the plasma.

40. (previously presented) The method of claim 38 wherein RF energy is supplied to the vaporization surface while a second electrode is held at ground potential to form the plasma.

41. (previously presented) The method of claim 38 wherein the vaporization surface is provided with a negative bias power while RF energy is supplied to a second electrode to form the plasma.

42. (previously presented) A method comprising:

flowing at least one liquid across a vaporization surface to form a vapor;

accumulating a deposition on the vaporization surface as a vapor is formed therefrom; and

using the vaporization surface as an electrode to form a plasma cleaning at least some of the deposition from the vaporization surface.

43. (previously presented) The method of claim 42 wherein the vaporization surface is comprised by a vapor forming device of a chemical vapor deposition apparatus.

44. (previously presented) The method of claim 42 wherein the vaporization surface is comprised by a chemical vapor deposition apparatus, wherein the at least one liquid comprises $Ba(THD)_2$, $Sr(THD)_2$ and $Ti(THD)_2(O\text{-}iPr)_2$, and further comprising chemical vapor depositing BST on a substrate within the apparatus.

45. (previously presented) The method of claim 42 wherein the plasma comprises one or more of gaseous Cl_2, CCl_4, CF_4, CHF_3, O_2, SF_6, NF_3, CCl_3F, $CClF_3$, $C2F_6$, H_2, C_3F_8, and O_3.

46. (previously presented) The method of claim 42 wherein the vaporization surface is held at ground potential while RF energy is supplied to a second electrode to form the plasma.

47. (previously presented) The method of claim 42 wherein RF energy is supplied to the vaporization surface while a second electrode is held at ground potential to form the plasma.

48. (previously presented) The method of claim 42 wherein the vaporization surface is provided with a negative bias power while RF energy is supplied to a second electrode to form the plasma.